CONFIG

Aixtron G5WW MOCVD for SiC Epitaxy

- Eight 6" wafers per batch
- Triple injector (top, center, bottom)
- Max. satellite temperature 1600℃
- EpiTune III for in-situ satellite temp. calibration
- 2-stage particle filter trap
- Source gases: SiH4, C3H8
- Dopant gases: N2, TMAl (internal bubbler)
- Process gases: H2, N2, Ar, HCl, 3.8% H2 in Ar
- Aixact version 8.1
- Two-stage dry process pump (Ebara ESA80 x2)
- Two scroll pumps for the Globe box (1) and the Antechamber (1)
- Horiba MFCs
- Process module 208VAC, RF Generator 380VAC
- No transfer modules, manual wafer loading/unloading
- 2016 vintage